



16N50K-MT

Preliminary

Power MOSFET

16A, 500V N-CHANNEL POWER MOSFET

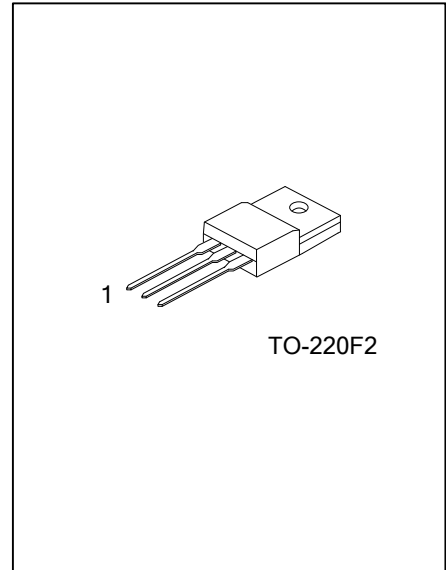
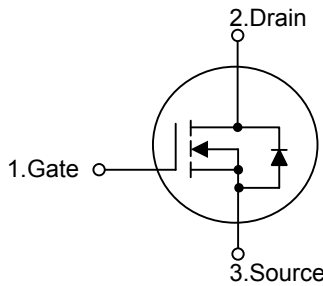
DESCRIPTION

The UTC **16N50K-MT** is a N-channel power MOSFET using UTC's advanced technology to provide the customers with minimum on-state resistance, superior switching performance and withstand high energy pulse in the avalanche and commutation mode.

FEATURES

- * $R_{DS(ON)} < 0.32\Omega @ V_{GS}=10V, I_D=8.0A$
- * High Switching Speed

SYMBOL



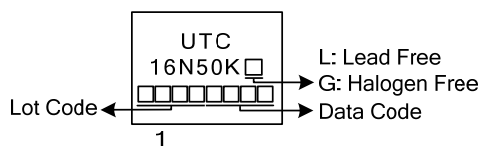
ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
16N50KL-TF2-T	16N50KG-TF2-T	TO-220F2	G	D	S	Tube

Note: Pin Assignment: G: Gate D: Drain S: Source

<p>16N50KL-TF2-T</p>	<p>(1) T: Tube</p> <p>(2) TF2: TO-220F2</p> <p>(3) L: Lead Free, G: Halogen Free and Lead Free</p>
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MARKING



■ ABSOLUTE MAXIMUM RATINGS ($T_C=25^\circ\text{C}$, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DSS}	500	V
Gate-Source Voltage		V_{GSS}	± 30	V
Drain Current	Continuous	I_D	16	A
	Pulsed (Note 2)	I_{DM}	64	A
Avalanche Energy	Single Pulsed (Note 3)	E_{AS}	1040	mJ
Peak Diode Recovery dv/dt		dv/dt	3.8	V/ns
Power Dissipation		P_D	62	W
Junction Temperature		T_J	+150	$^\circ\text{C}$
Storage Temperature		T_{STG}	-55 ~ +150	$^\circ\text{C}$

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Repetitive Rating: Pulse width limited by maximum junction temperature.

3. $L = 144 \text{ mH}$, $I_{AS} = 3.8 \text{ A}$, $V_{DD} = 50 \text{ V}$, $R_G = 25 \Omega$, Starting $T_J = 25^\circ\text{C}$

4. $I_{SD} \leq 16 \text{ A}$, $di/dt \leq 200 \text{ A}/\mu\text{s}$, $V_{DD} \leq BV_{DSS}$, Starting $T_J = 25^\circ\text{C}$

■ THERMAL DATA

PARAMETER	SYMBOL	RATING	UNIT
Junction to Ambient	θ_{JA}	62.5	$^\circ\text{C}/\text{W}$
Junction to Case	θ_{JC}	2.01	$^\circ\text{C}/\text{W}$

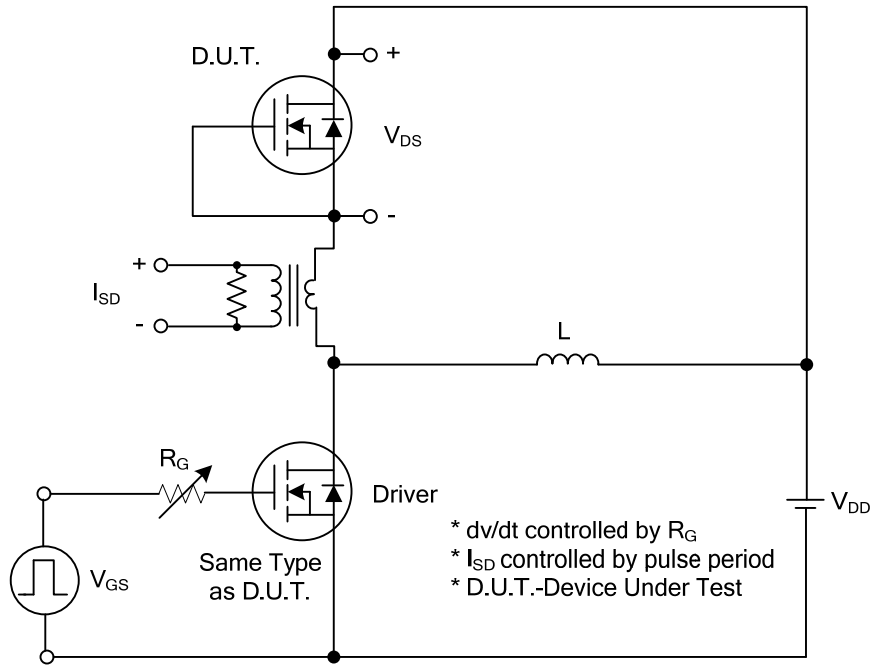
■ ELECTRICAL CHARACTERISTICS ($T_C=25^\circ\text{C}$, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV_{DSS}	$I_D=250\mu\text{A}$, $V_{GS}=0\text{V}$	500			V
Drain-Source Leakage Current	I_{DSS}	$V_{DS}=500\text{V}$, $V_{GS}=0\text{V}$				μA
Gate- Source Leakage Current	Forward	I_{GSS}			+100	nA
	Reverse					
ON CHARACTERISTICS						
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{DS}=V_{GS}$, $I_D=250\mu\text{A}$	2.0		4.0	V
Static Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS}=10\text{V}$, $I_D=8.0\text{A}$			0.32	Ω
DYNAMIC PARAMETERS						
Input Capacitance	C_{ISS}	$V_{GS}=0\text{V}$, $V_{DS}=25\text{V}$, $f=1.0\text{MHz}$		1800		pF
Output Capacitance	C_{OSS}			240		pF
Reverse Transfer Capacitance	C_{RSS}			9		pF
SWITCHING PARAMETERS						
Total Gate Charge (Note 1)	Q_G	$V_{DS}=50\text{V}$, $V_{GS}=10\text{V}$, $I_D=1.3\text{A}$ $I_G=100\mu\text{A}$ (Note 1, 2)		62		nC
Gate to Source Charge	Q_{GS}			11		nC
Gate to Drain Charge	Q_{GD}			16		nC
Turn-ON Delay Time (Note 1)	$t_{D(ON)}$	$V_{DS}=30\text{V}$, $V_{GS}=10\text{V}$, $I_D=0.5\text{A}$, $R_G=25\Omega$ (Note 1, 2)		110		ns
Rise Time	t_R			142		ns
Turn-OFF Delay Time	$t_{D(OFF)}$			354		ns
Fall-Time	t_F			124		ns
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS						
Maximum Body-Diode Continuous Current	I_S				16	A
Maximum Body-Diode Pulsed Current	I_{SM}				64	A
Drain-Source Diode Forward Voltage (Note 1)	V_{SD}	$I_S=16\text{A}$, $V_{GS}=0\text{V}$			1.4	V
Body Diode Reverse Recovery Time (Note 1)	t_{RR}	$I_S=16\text{A}$, $V_{GS}=0\text{V}$		404		ns
Reverse Recovery Charge	Q_{RR}	$di/dt=100\text{A}/\mu\text{s}$ (Note 1)		6		μC

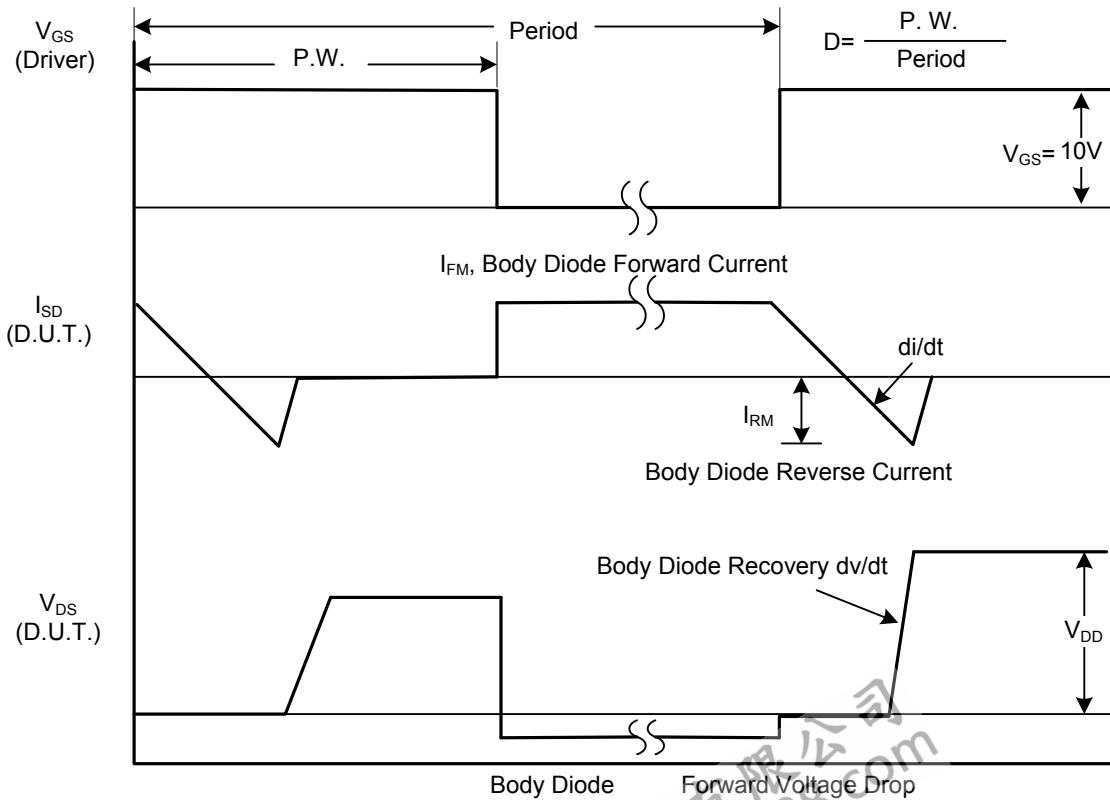
Notes: 1. Pulse Test: Pulse width $\leq 300\mu\text{s}$, Duty cycle $\leq 2\%$.

2. Essentially independent of operating temperature.

TEST CIRCUITS AND WAVEFORMS

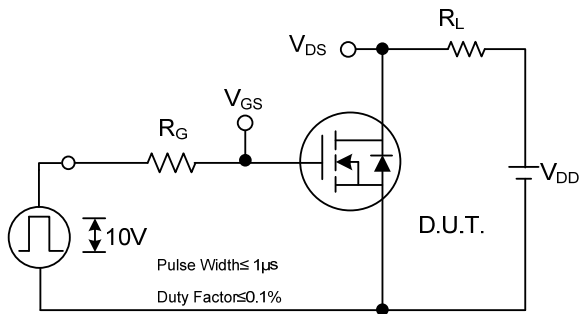


Peak Diode Recovery dv/dt Test Circuit

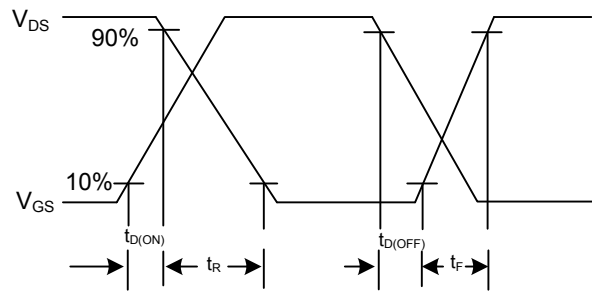


Peak Diode Recovery dv/dt Waveforms

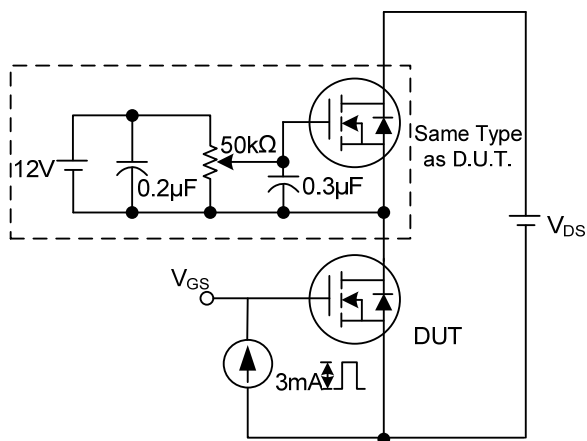
TEST CIRCUITS AND WAVEFORMS (Cont.)



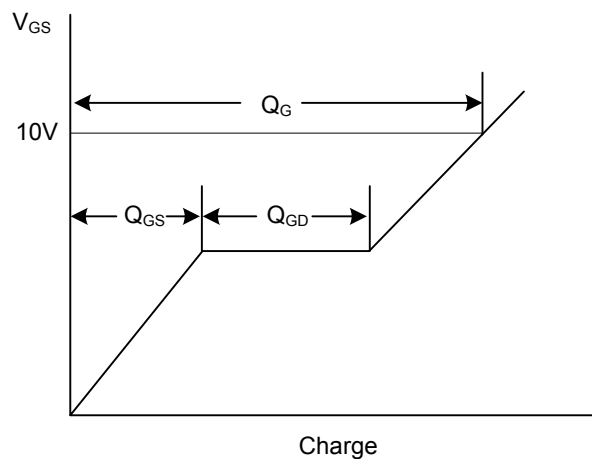
Switching Test Circuit



Switching Waveforms

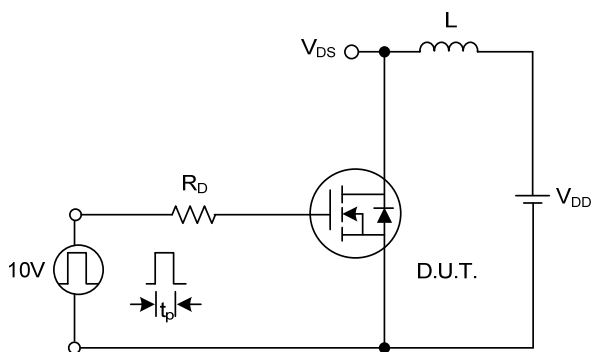


Gate Charge Test Circuit

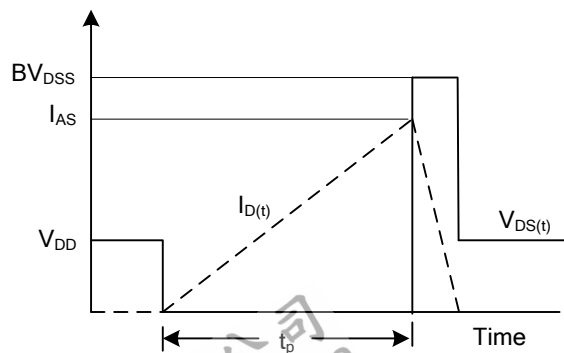


Charge

Gate Charge Waveform



Unclamped Inductive Switching Test Circuit



Unclamped Inductive Switching Waveforms

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